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SOT-89 NPN Silicon NPN transistor in a SOT-89 Plastic Package.

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, , 2SA1201

High f_T, high V_{CEO}, small flat package, complementary pair with 2SA1201.

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Power amplifier applications.

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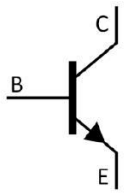

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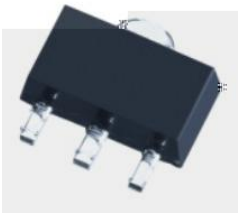

PIN1 Base PIN 2 Collector PIN 3 Emitter

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h_{FE} Classifications Symbol	O	Y
h_{FE} Range	80 160	120 240
Marking	HCO ⁑	HCY⁑

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	120	V
Collector to Emitter Voltage	V_{CEO}	120	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current-Continuous	I_C	800	mA
Collector Base-Continuous	I_B	160	mA
Collector Power Dissipation	P_C	500	mW
Collector Power Dissipation*	*P_C	1.0	W

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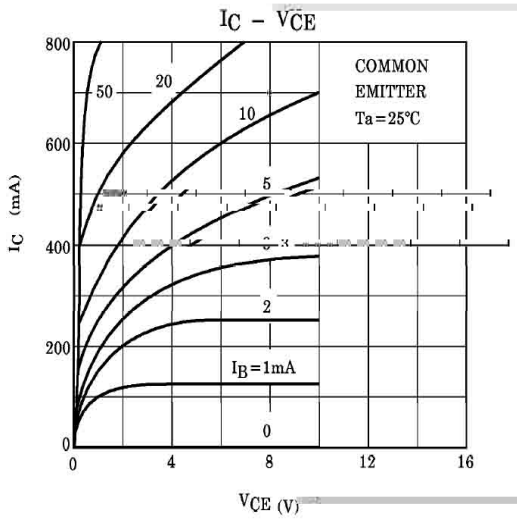
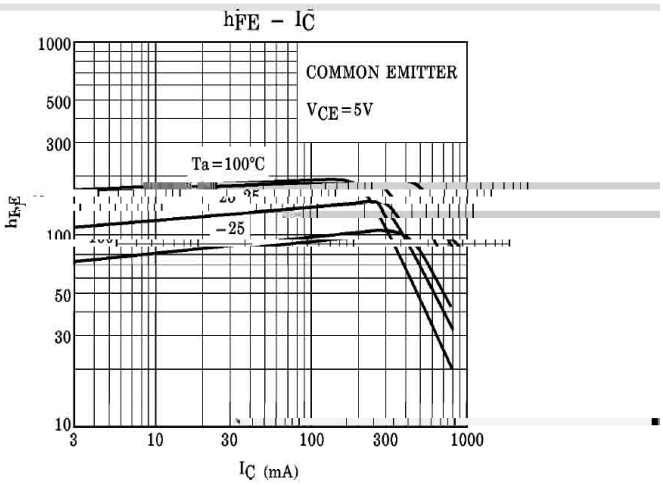
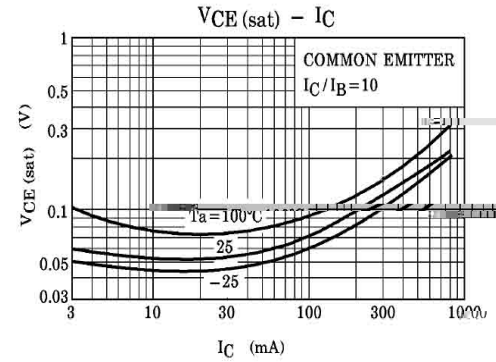
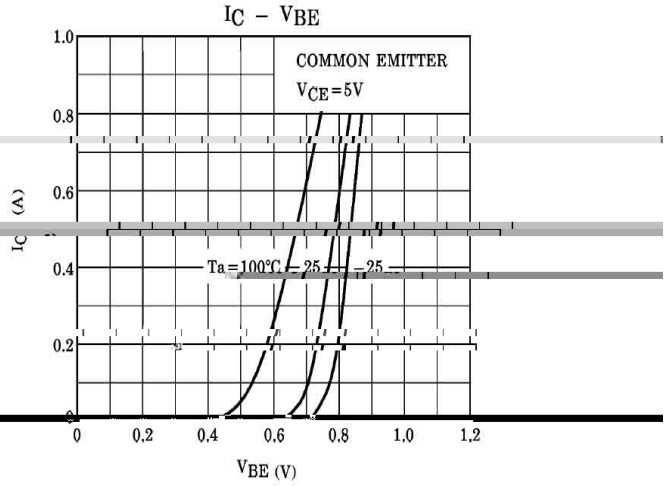
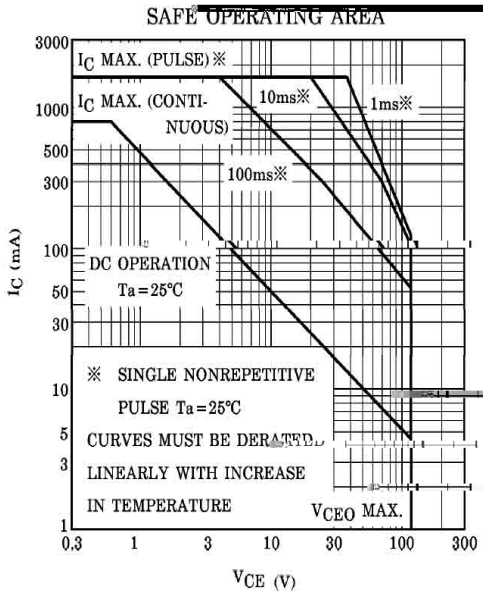
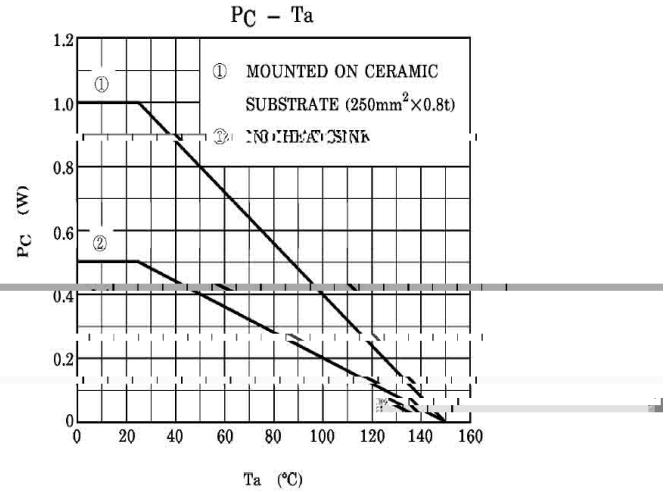

IC – VCE
COMMON EMITTER
Ta=25°C
IB=1mA
IC (mA)
VCE (V)


hFE – IC
COMMON EMITTER
VCE=5V
Ta=100°C
−25
IC (mA)


VCE (sat) – IC
COMMON EMITTER
IC/IB=10
Ta=100°C
25
−25
VCE (sat) (V)
IC (mA)


IC – VBE
COMMON EMITTER
VCE=5V
Ta=100°C
25
−25
IC (A)
VBE (V)


SAFE OPERATING AREA
IC MAX. (PULSE)※
IC MAX. (CONTINUOUS)
10ms※
1ms※
100ms※
DC OPERATION
Ta=25°C
※ SINGLE NONREPETITIVE PULSE Ta=25°C
CURVES MUST BE DERATED LINEARLY WITH INCREASE IN TEMPERATURE
VCEO MAX.
IC (mA)
VCE (V)


PC – Ta
① MOUNTED ON CERAMIC SUBSTRATE (250mm²×0.8t)
PC (W)
Ta (°C)

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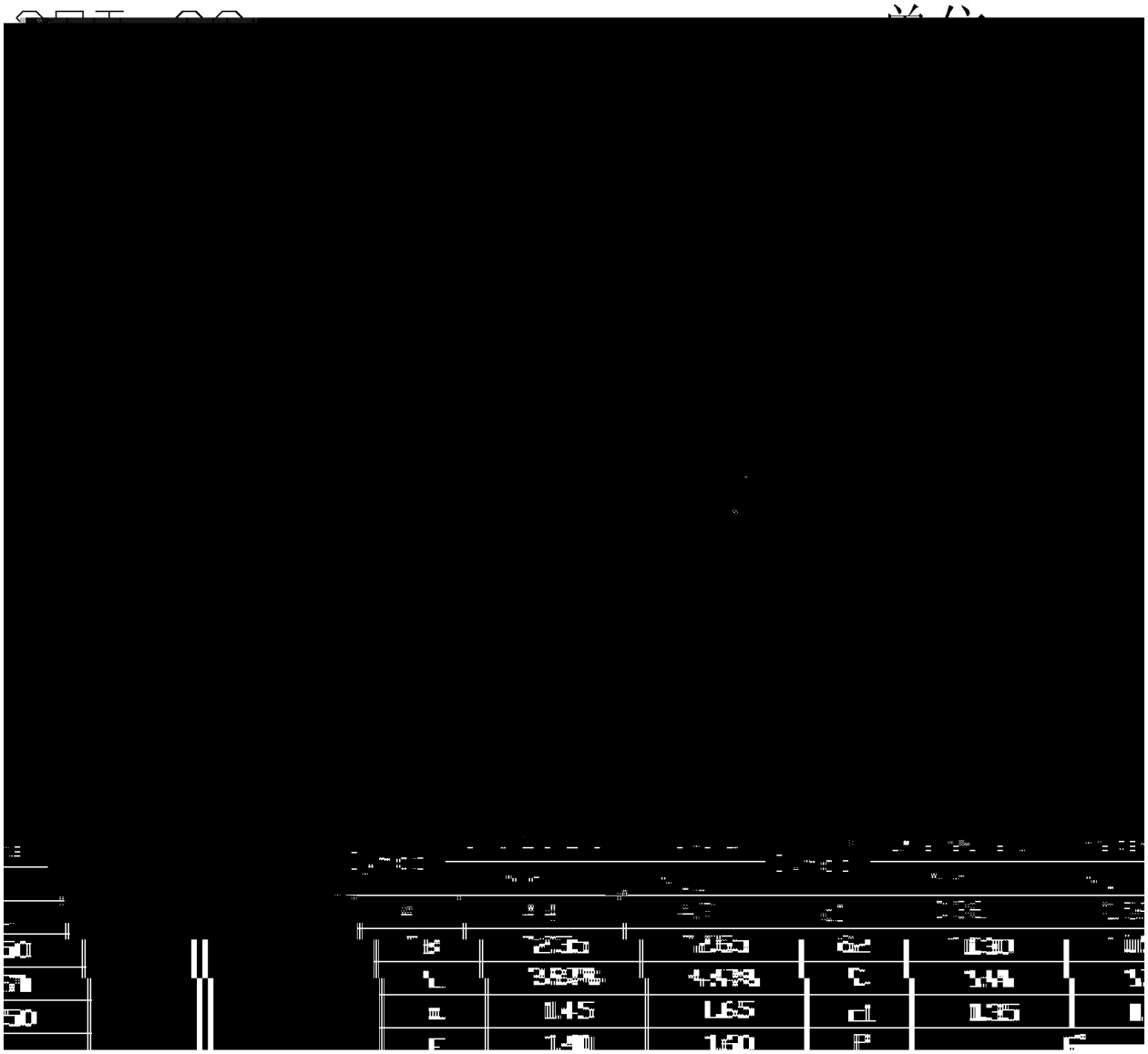

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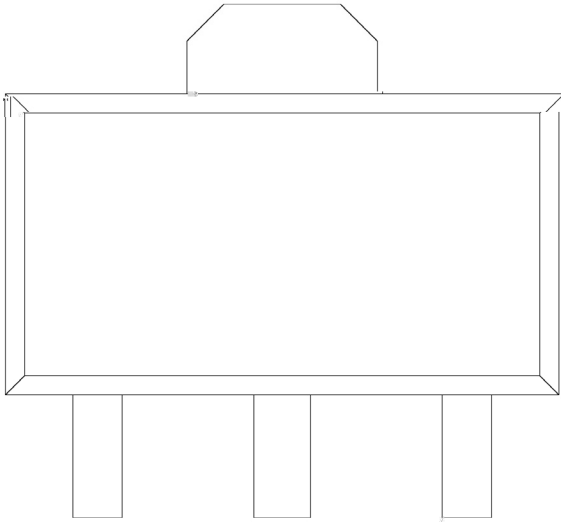

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Note:

H: Company Code.

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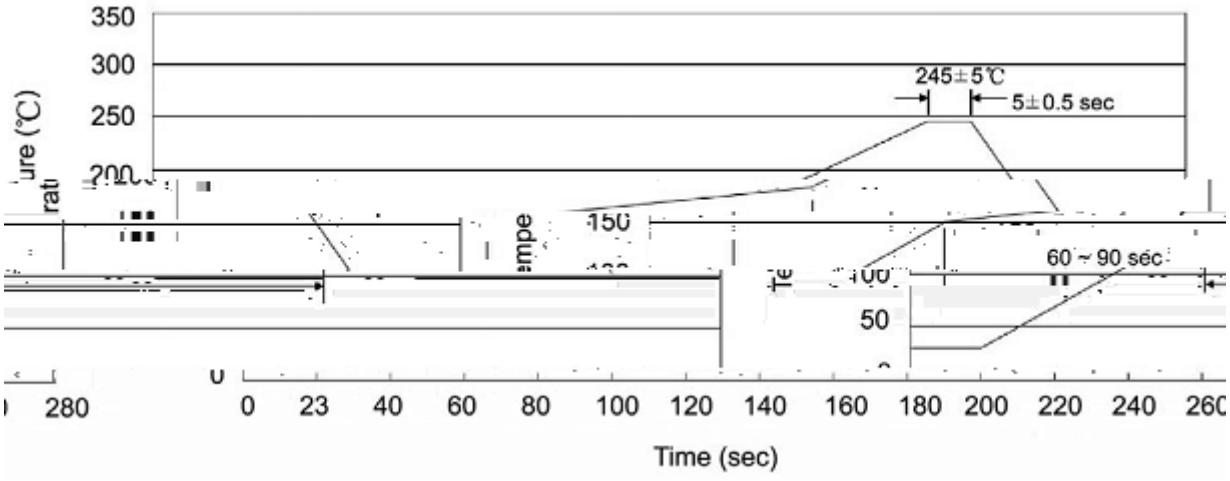

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1	25 150	60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2	245±5	5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3	2 10 /sec.		3. Cooling Speed: 2~10 /sec.

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ɜ̈ 260±5 ɜ̈ 10±1 sec. Temp.:260±5 Time:10±1 sec

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/ REEL

Package Type	Units					Dimension (unit mm^3)		
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
SOT-89	1,000	7	7,000	8	56,000	7 ×12	180×120×180	385×257×392

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